



Features

- Ultra-low operating supply voltage:
XO5027LVC1/B1-C-V: 0.9V to 2.0V
XO5027LVCy/By-C-V: 1.05V to 2.0V, $y \geq 2$
- Low crystal drive current oscillation for miniature crystal units
- XO5027LVC/B series: for Wire Bonding
XO5027LVCy-C-V: C type package
XO5027LVBy-C-V: B type package
- -40 to 125°C operating temperature range
- Crystal frequency (10MHz~50MHz)
- Output Freq: Crystal Freq divided by 1/2/4/8/16
- Very low standby current
- 50±5% output duty cycle
- 15pF output drive capability
- Die form or Wafer form
- AEC-Q100 qualified. PPAP capable, and manufactured in IATF 16949 certified facilities.

Description

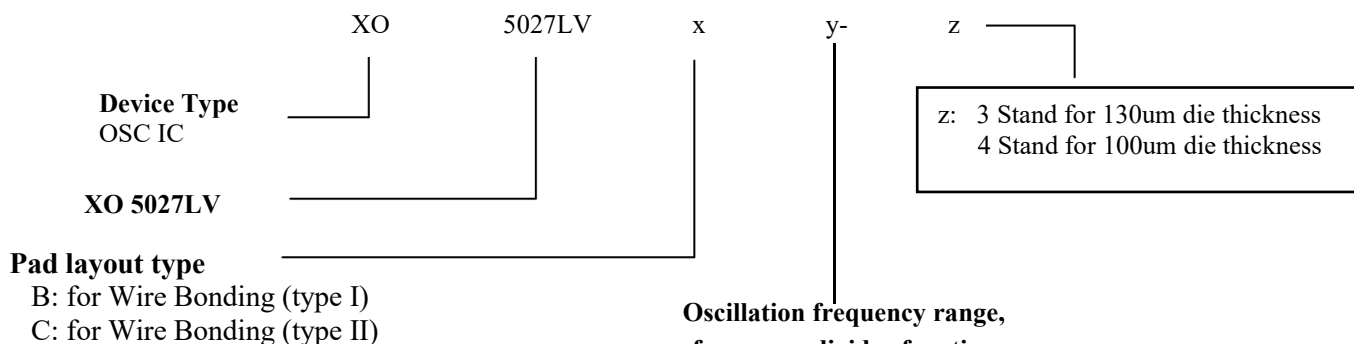
The XO5027LVCy/By-C-V series are miniature crystal oscillator module ICs. The oscillator circuit stage has constant current drive, significantly reducing current consumption and crystal current, compared with existing devices, and significantly reducing the oscillator characteristics supply voltage dependency.

Applications

- Fundamental Crystal Oscillator
- 7050, 5032, 3225, 2520, 2016 crystal oscillator

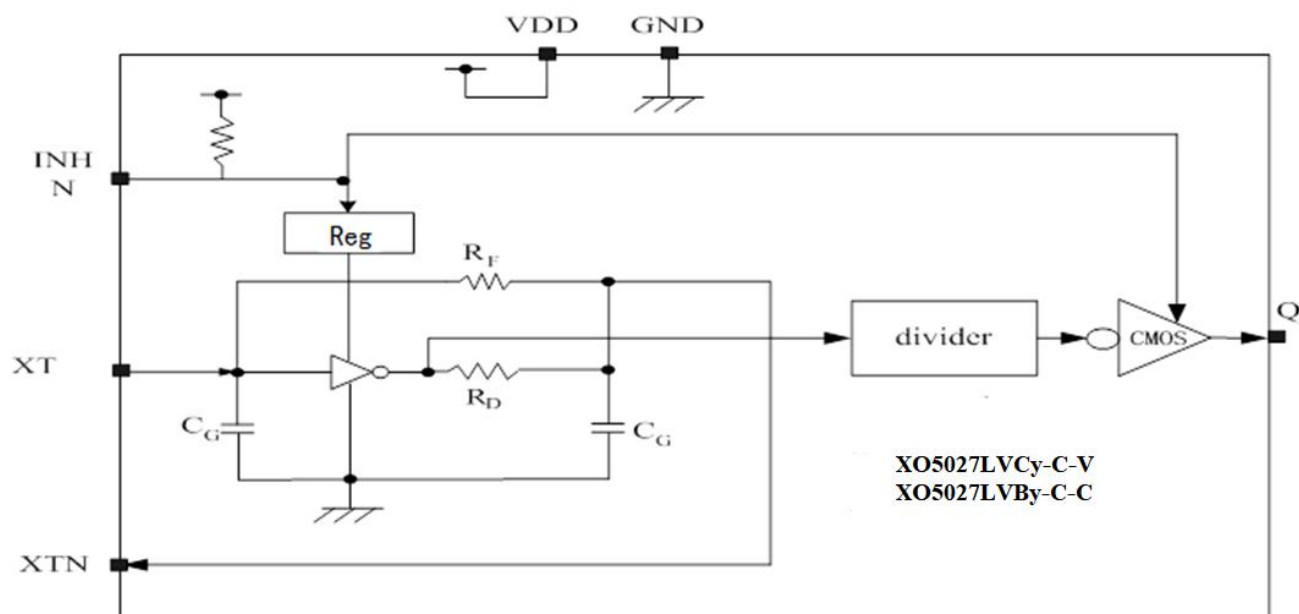
Ordering Information

Part no.	Package type
XO5027LVxy-zWF-C-V	Wafer form
XO5027LVxy-zDE-C-V	Die form





Block Diagram



Function Description

Standby Function

When INHN goes LOW, the oscillator stops and the output on Q becomes high impedance.

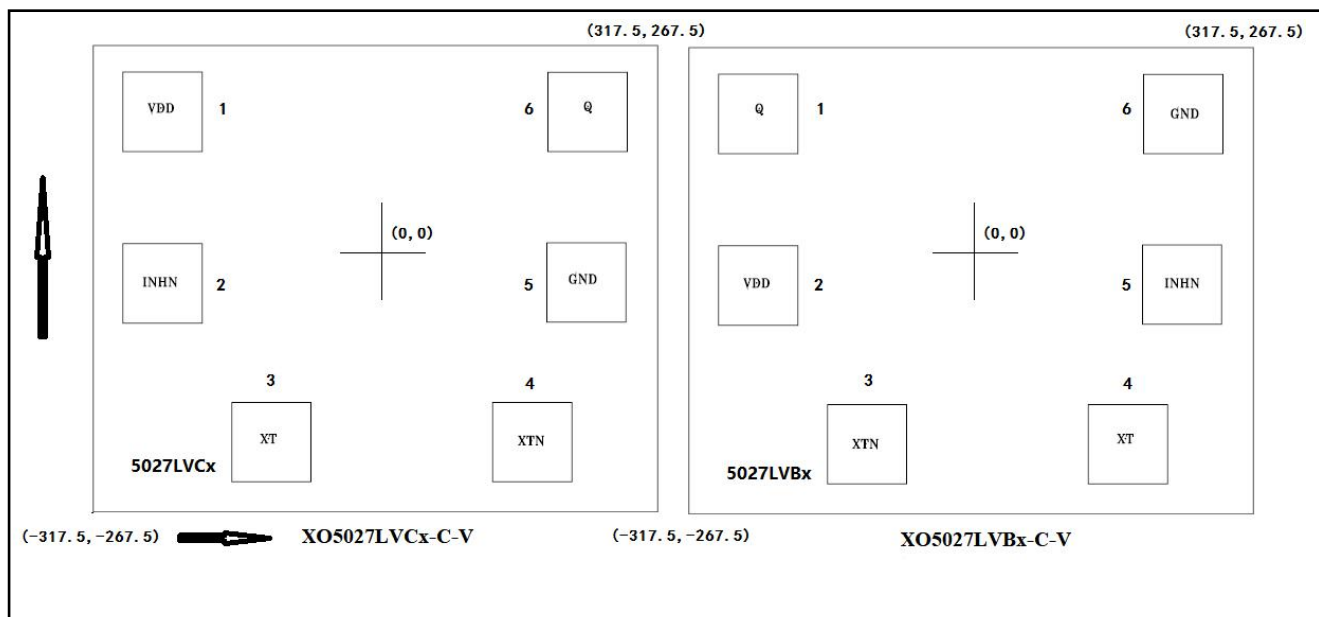
INHN	Q	Oscillator
HIGH (or open)	$F_O/1/2/4/8/16$ output frequency	Normal operation
Low	High impedance	Stopped

Power-saving Pull-up Resistor

The INHN pin pull-up resistance RUP1 or RUP2 changes in response to the input level (HIGH or LOW). When INHN is tied LOW level, the pull-up resistance is large (RUP1), reducing the current consumed by the resistance. When INHN is left open circuit, the pull-up resistance is small (RUP2), which increases the input susceptibility to external noise. However, the pull-up resistance ties the INHN pin HIGH level to prevent external noise from unexpectedly stopping the output.



Pad Configuration



Pad Coordinate File					
Pad Name	X Coordinate	Y Coordinate	Pad Name	X Coordinate	Y Coordinate
1	-214.85	168	4	158.35	-164.6
2	-214.85	-4.65	5	213.15	-3.85
3	-105.1	-164.6	6	214.2	167.9

Note: Substrate is connected to GND or floating.

Die Size: 570μm*470μm (Don't include scribe line, Scribe Line:65μm)

Die Thickness: 130μm±15μm (-3) or 100μm±15μm (-4)

Pad Size: 80μm*80μm **Substrate Level:** GND or Floating

Pad Description

Sym.	Type	Description	
XTN	O	Amplifier output.	Crystal oscillator connected between XT and XTN.
XT	I	Amplifier input.	
INHN	I	Output state control input. Output High Impedance when LOW. Power-saving pull-up resistor built in. When V _{DD} <1V, Required External High-Level input to enable output.	
V _{DD}	P	Supply voltage.	
GND	P	Ground.	
Q	O	Output. Output frequency determined by fundamental crystal (f0 divided by 1/2/4/8/16).	



Maximum Ratings

Storage Temperature.....	-65°C to +150°C
Supply Voltage to Ground Potential (V_{DD} to GND).....	-0.5V to +5.5V
DC Input (All Other Inputs except V_{DD} & GND)..	-0.5V to $V_{DD} + 0.5V$
DC Output.....	-0.5V to $V_{DD} + 0.5V$
DC Output Current (all outputs).....	20mA

Note: Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Recommended Operating Conditions

(GND=0V, unless otherwise noted.)

Sym.	Parameter	Conditions	Min	Typ.	Max	Unit
V_{DD}	Supply voltage	XO5027LVC1/B1-C-V	0.9	-	2.0	V
V_{DD}	Supply voltage	XO5027LVCy/By-C-V, $y \geq 2$	1.05	-	2.0	V
T_A	Operating temperature	-	-40	-	+125	°C
f_0	Oscillation frequency* ¹	-	10	-	50	MHz



DC Electrical Characteristics

XO5027LVCy/By-C-V ($V_{DD} = 1.1$ to $2.0V$, $T_A = -40$ to $125^\circ C$, unless otherwise noted.)

Parameter	Sym	Conditions	Min	Typ.	Max	Unit
HIGH-level output voltage	V_{OH}	$I_{OH}=1mA$	$V_{DD}-0.4$	-	-	V
LOW-level output voltage	V_{OL}	$I_{OL}=1mA$	-	-	0.4	
HIGH-level input voltage	V_{IH}	OE Measurement	$0.8V_{DD}$	-	-	V
LOW-level input voltage	V_{IL}	OE Measurement	-	-	$0.2V_{DD}$	
Operating Current	I_{CC}	$V_{DD}=1.1V$ (25MHz/10pf)	-	0.9	1.4	mA
Operating Current	I_{CC}	$V_{DD}=1.8V$ (25MHz/10pf)	-	2.2	3.3	mA
Operating Current	I_{CC}	$V_{DD}=1.1V$ (50MHz/10pf)	-	1.6	2.4	mA
Operating Current	I_{CC}	$V_{DD}=1.8V$ (50MHz/10pf)	-	3.4	5.0	mA
Standby Current	I_{sb}	OE=off	-	-	10	uA
OE pull-up resistance	-	-	-	-	-	-
	R_{PULL}	$V_{DD}=1.8V$	-	5	10	MΩ
Output leakage current	I_Z	OE=OFF $V_O = V_{DD}$	-	-	10	μA

AC Characteristics

XO5027LVCy/By-C-V, $T_A = -40$ to $125^\circ C$ unless otherwise noted

Parameter	Symbol	Condition		Min	Typ.	Max	Unit
Output Disable Delay	t _{OD}	Output Disable Function (OE)		-	-	500	ns
Output Enable Delay	t _{STR}	Output Enable Function (OE)		-	-	10	ms
Output rise time	t _{r1}	25MHz/10pf, 0.2V _{DD} to 0.8V _{DD}	V _{DD} =1.2V	-	1.5	3.0	ns
	t _{r2}		V _{DD} =1.5V	-	1.0	2.0	ns
	t _{r3}		V _{DD} =1.8V	-	0.8	1.6	ns
Output fall time	t _{f1}	25MHz/10pf, 0.8V _{DD} to 0.2V _{DD}	V _{DD} =1.2V	-	1.5	3.0	ns
	t _{f2}		V _{DD} =1.5V	-	1.0	2.0	ns
	t _{f3}		V _{DD} =1.8V	-	0.8	1.6	ns
Output duty cycle	Duty	T _A =25°C, C _L =10pF		45	50	55	%
V _{DD} Sensitivity Frequency vs. V _{DD} +/-10%	-	Frequency vs. V _{DD} +/-10%		-5	-	+5	ppm
OSC frequency range	f _R	Fundamental Crystal		10	-	50	MHz

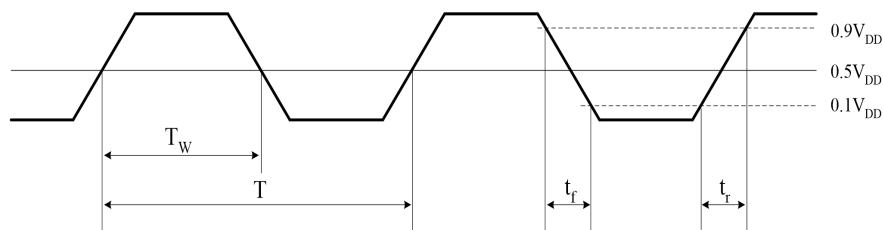
Crystal Specifications

Parameters	Sym	Conditions	Min	Typ.	Max	Units
Fundamental Crystal Resonator Frequency (XO5027LVCy/By-C-V)	F_{XIN}	-	10	-	50	MHz
Maximum Sustainable Drive Level	-	-	-	-	100	μW
Operating Drive Level	-	-	-	30	-	μW
Crystal Shunt capacitance	C_O	-	-	-	4	pF
Effective Series Resistance, Fundamental, 10-50MHz	ESR	-	-	-	30	Ω



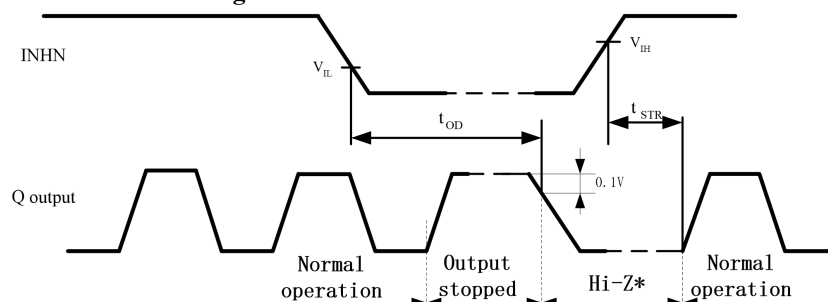
AC Electrical Characteristics

Output switching waveform



$$\text{DUTY} = T_W / T \times 100 (\%)$$

Output disable and oscillation start timing chart



When INHN goes HIGH to LOW, the Q output goes HIGH once and then becomes high impedance.

When INHN goes LOW to HIGH, the Q output from high impedance to normal output operation when the oscillation starts (oscillation is detected)

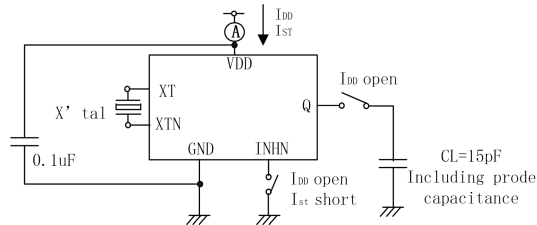
*: the high –impedance interval in the figure is shown as a LOW level due to the $1K\Omega$ pull-down resistor connected to the Q pin(see“Measurement circuit 2”in the “Measurement circuits” section)



Measurement Circuit

Measurement cct1

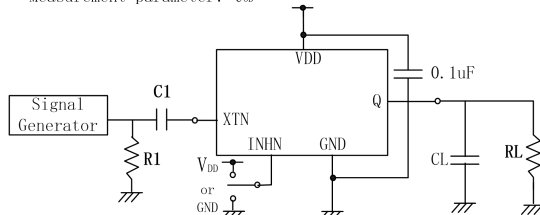
Measurement parameter: I_{DD} , I_{ST} , Duty, t_r , t_f



Note: The AC characteristics are observed using an oscilloscope on pin Q

Measurement cct2

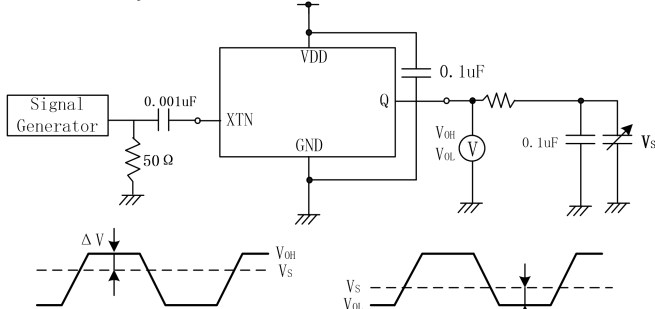
Measurement parameter: t_{DD}



XTN input signal: 1Vp-p, sine wave
C1: 0.001uF CL: 15pF
R1: 50 Ω RL: 1K Ω

Measurement cct3

Measurement parameter: V_{OH} , V_{OL}



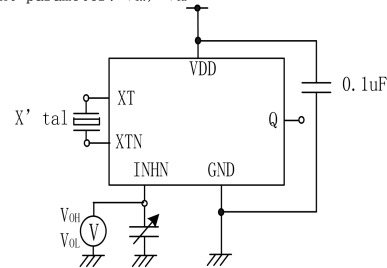
V_S adjusted such that $\Delta V = 50 \times I_{OH}$

V_S adjusted such that $\Delta V = 50 \times I_{OL}$

XTN input signal: 1Vp-p, sine wave

Measurement cct4

Measurement parameter: V_{IH} , V_{IL}



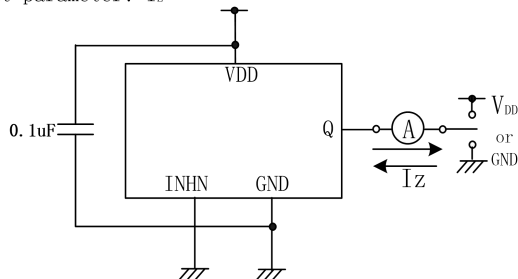
V_{IH} : Voltage is 0V to V_{DD} transition that changes the output state.

V_{IL} : Voltage is V_{DD} to 0V transition that changes the output state.

INHN has an oscillation stop function

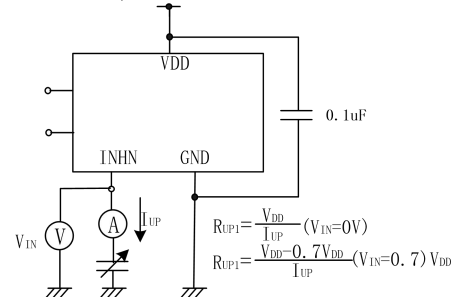
Measurement cct5

Measurement parameter: I_Z



Measurement cct6

Measurement parameter: R_{UP1} , R_{UP2}



$$R_{UP1} = \frac{V_{DD}}{I_{UP}} (V_{IN} = 0V)$$

$$R_{UP1} = \frac{V_{DD} - 0.7V_{DD}}{I_{UP}} (V_{IN} = 0.7)V_{DD}$$



Revision History:

Revision	Description	Date
V1.0	Official release	2025/12/23